Given
$$V_T = 1V$$

$$K = 0.25 \text{mA/V}^2$$

$$2k\Omega$$

$$V_{DD} = 8V$$

$$2k\Omega$$

$$V_D$$

$$V_D$$

$$V_D$$

$$V_D$$

$$V_D$$

$$V_S$$

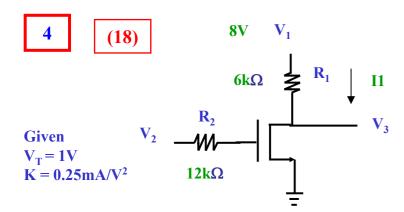
Find V_{DS} and I_{DS} for $V_G = 3.5V$

MOS is in saturation mode

$$I_{DS} = K (V_{GS} - V_T)^2 = 0.25m(3.5 - 1)^2 = 1.5625mA$$

$$\therefore V_{DS} = V_{DD} - I_{DS}R_D = 8 - (1.5625m)2k \cong 4.875V$$

$$\therefore \mathbf{I_{DS}} = \frac{8 - 4.875}{2\mathbf{k}} = 1.5625 \mathbf{mA}$$



a

If
$$V_2 = 0.5V$$

$$V_{GS} < V_{T}$$

0.5 < 1

$$\mathbf{I}_1 = 0$$

NMOS cut off

$$\therefore V_3 = 8V$$

b

If
$$V_2 = 3V$$

Assume NMOS is in saturation

:
$$I_1 = K (V_{GS} - V_T)^2 = 0.25m(3-1)^2 = 1mA$$

$$V_3 = 8 - I_1 R_1 = 8 - 1m(6k) = 2V$$

NMOS is saturated since

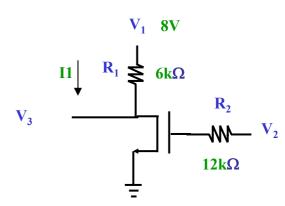
1.
$$3 > 1$$

$$2. 2 = 3 - 1$$

NMOS is saturated since

1.
$$V_{GS} > V_{T}$$

2.
$$V_{DS} = V_{GS} - V_{T}$$



4. (a) If V_2 = 0.5V, find I_1 and V_3 . (b) If V_2 = 2V, find I_1 and V_3 . State clearly the reasons for your answer.

Given $V_T = 1V$, $K = 0.25 \text{mA/V}^2$.

Given that

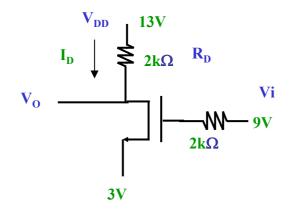
at triode region, $I_{DS} = 2K[(V_{GS} - V_T)V_{DS} - V_{DS}^2/2]$

at saturation region,

$$I_{DS} = K[(V_{GS} - V_{T})^{2}]$$

(19).

(26)



Given
$$V_T = 1V$$
 $K = 0.5 \text{mA/V}^2$

$$\therefore \mathbf{I}_{\mathbf{D}} = \frac{\mathbf{V}_{\mathbf{D}\mathbf{D}} - \mathbf{V}_{\mathbf{D}\mathbf{S}}}{\mathbf{R}_{\mathbf{D}}} = \frac{10 - \mathbf{V}_{\mathbf{D}\mathbf{S}}}{2\mathbf{k}}$$

$$= 2\mathbf{K}[(\mathbf{V_{GS}} - \mathbf{V_{T}})\mathbf{V_{DS}} - \frac{\mathbf{V_{DS}}^2}{2}] = 1\mathbf{m}[(8 - 2 - 1)\mathbf{V_{DS}} - \frac{\mathbf{V_{DS}}^2}{2})]$$

$$\therefore \frac{10 - \mathbf{V_{DS}}}{2\mathbf{k}} = 1\mathbf{m}[5\mathbf{V_{DS}} - \frac{\mathbf{V_{DS}}^2}{2}]$$

$$\therefore 10 - \mathbf{V_{DS}} = 2[5\mathbf{V_{DS}} - \frac{\mathbf{V_{DS}}^2}{2}]$$

$$V_{DS}^2 - 11V_{DS} + 10 = 0$$

$$\therefore \mathbf{V}_{\mathbf{DS}} = 10\mathbf{V} \quad \mathbf{or} \quad 1\mathbf{V}$$

$$\begin{aligned} &\text{hence} \ \ V_O = 3 + 1 = 4V \\ &V_{DS} = 12 \ V = V_{DD} \ \ \text{is impossible since MOS is not} \\ &\text{cut off} \ \ \ (V_{DGS} > V_T) \end{aligned}$$

NMOS is in triode since

1.
$$V_{GS} > V_T$$

$$2. V_{DS}^{OS} < V_{GS} - V_{T}$$

NMOS is triode since

1.
$$6 > 1$$

$$2. 1 < 6 - 1$$

$$\therefore \mathbf{I}_{D} = 2\mathbf{K}[(\mathbf{V}_{GS} - \mathbf{V}_{T})\mathbf{V}_{DS} - \frac{\mathbf{V}_{DS}^{2}}{2}]$$
$$= 1\mathbf{m}[(6-1)1 - \frac{1}{2})] = 4.5\mathbf{m}\mathbf{A}$$

5. In the circuit, find $\boldsymbol{V}_{\mathrm{O}}\,$. State clearly the reasons for your answer.

Given $V_T = 1V$, $K = 0.5 \text{mA/V}^2$.

Given that

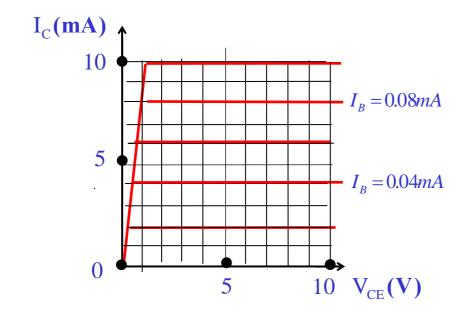
at triode region, $I_{DS} = 2K[(V_{GS}-V_T)V_{DS}-V_{DS}^2/2]$

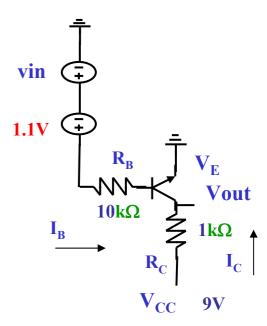
at saturation region,

$$I_{DS} = K[(V_{GS} - V_T)^2]$$

(26).

- 8. A BJT with the following I_C - V_{CE} characteristics is used in the following circuit. (a) Sketch the load line V_{CE} = V_{CC} I_CR_C and the Q point on the graph.
- (b) If vin = 0.1 cos ωt V, sketch the base current I_B , the collector current I_C and the output voltage Vout. Show clearly the DC value, the maximum and minimum value in your sketch. Estimate also the current gain dI_C/dI_B and voltage gain dVout / dVin.
- (c) Sketch the small signal (AC) equivalent circuit of the amplifier and find the voltage gain Av (= Vout/Vin). For the BJT, given $r\pi=0\Omega$, $V_{BE(ON)}=0.7V$. (49)







1.2

 $V_{in} + v_{in}(V)$

1.0

Find I_B from equation

 $\begin{array}{c} 50 \\ 40 \\ \end{array} \bigcirc \begin{array}{c} \cdot \cdot \cdot I_{B} \\ \end{array}$

 $I_{B} = \frac{\mathbf{V}_{in} - \mathbf{V}_{BE}}{\mathbf{R}_{B}} = \frac{1.1\mathbf{V} - 0.7\mathbf{V}}{10\mathbf{k}\Omega} = 0.04\mathbf{m}\mathbf{A}$

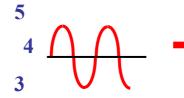
30

 $I_B + i_B (\mu A)$

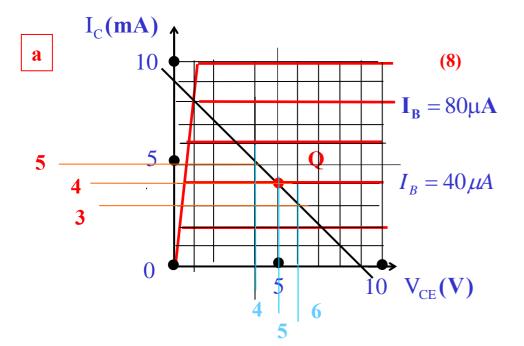
c

Find V_{CE} from graph

 $I_C + i_C$ (mA)



 $\begin{array}{c}
6 \\
5 \\
4
\end{array}$ $V_{CE} + V_{CE}(V)$

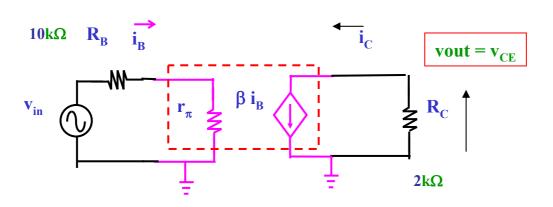


Estimate current and voltage gain

$$\therefore \mathbf{A}_{\mathbf{I}} = \boldsymbol{\beta}_{\mathbf{F}} = \frac{\Delta \mathbf{I}_{\mathbf{C}}}{\Delta \mathbf{I}_{\mathbf{B}}} \approx \frac{5\mathbf{m} - 3\mathbf{m}}{50\mu - 30\mu} = \frac{2\mathbf{m}\mathbf{A}}{20\mu\mathbf{A}} = 100$$

:.
$$A_{V} = \frac{\Delta V_{out}}{\Delta V_{in}} = \frac{6V - 4V}{1.0V - 1.2V} = \frac{2V}{-0.2V} = -10$$

c

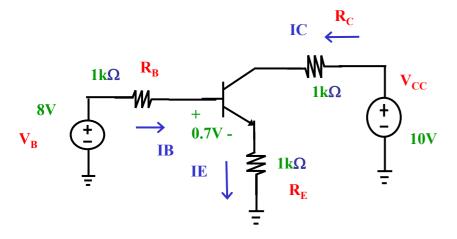


$$\therefore \mathbf{A}\mathbf{v} = \frac{\mathbf{v}_{\text{OUT}}}{\mathbf{v}_{\text{in}}} = \frac{-\beta \, \mathbf{i}_{\text{B}} \mathbf{R}_{\text{C}}}{\mathbf{i}_{\text{B}} (\mathbf{R}_{\text{B}} + \mathbf{r}_{\pi})} = \frac{-\beta \mathbf{R}_{\text{C}}}{\mathbf{R}_{\text{B}} + \mathbf{r}_{\pi}} = \frac{-(100)(1\mathbf{k})}{10\mathbf{k}} \cong -10$$

9. Given the BJT circuit.

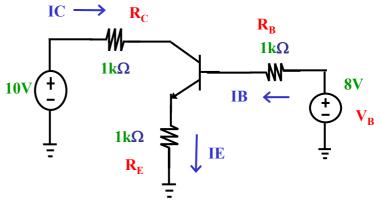
Given that IB is about 1.57mA. Show that the BJT is in saturation. Hence show that the forced beta is about 2.7.

For the BJT, given $\boldsymbol{V}_{BE}=0.7V,\,\beta=100,\,\boldsymbol{V}_{CESAT}=0.1V$. (30)



:.
$$I_C = \beta I_B = 100(1.57 \text{m}) = 157 \text{mA}$$

>> $I_C \text{ (when } V_{CE} = 0 \text{V)} = \frac{10 \text{V}}{2 \text{k} \Omega} = 5 \text{mA}$



$$\therefore I_{B} = \frac{V_{B} - V_{BE}}{R_{B} + (1 + \beta^{*})R_{E}} = \frac{V_{CC} - V_{CESAT}}{\beta^{*}R_{C} + (1 + \beta^{*})R_{E}}$$

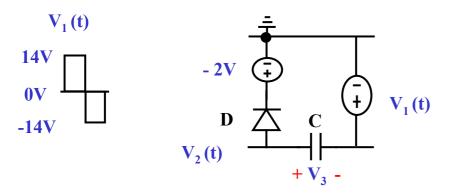
$$I_{\mathbf{B}} = \frac{8 - 0.7}{1\mathbf{k} + (1 + \beta^*)1\mathbf{k}} = \frac{10 - 0.1}{1\mathbf{k}(1 + 2\beta^*)}$$

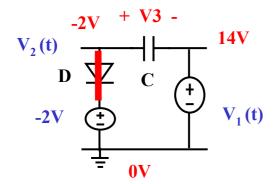
$$\therefore 7.3(1+2\beta^*) = 9.9(2+\beta^*)$$

$$\therefore 14.6\beta * +7.3 = 9.9\beta * +19.8$$

$$\beta^* = \frac{19.8 - 7.3}{14.6 - 9.9} \cong 2.66$$

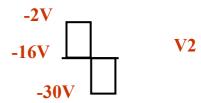
11. (a) In the ideal diode circuit, find V3 and sketch V2(t). (15)





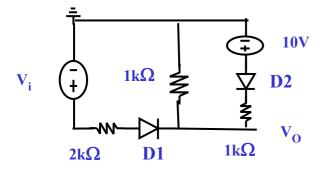
Hence V3 = -16V

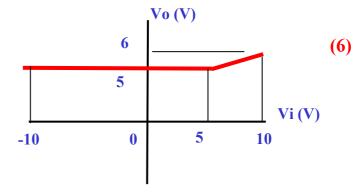
Hence $V_2 = V1 + V3 = V1 - 16V$



(b) In the ideal diode circuit, plot Vo versus Vi for $-10V \le Vi \le 10V$.

Show clearly all voltages in your sketch. (20)





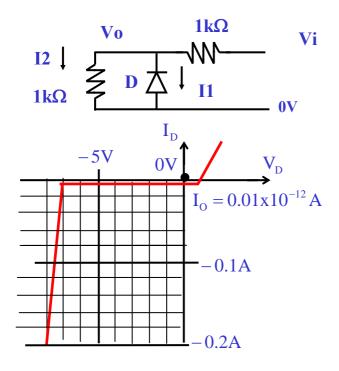
Vi < 5V, D1 OFF and D2 ON

$$\therefore$$
 Vo = 5V

Vi > 5V, D1 and D2 ON,

$$\therefore \frac{\text{Vi} - \text{Vo}}{2\text{k}} + \frac{10 - \text{Vo}}{1\text{k}} = \frac{\text{Vo}}{1\text{k}}$$
$$\therefore \text{Vi} - \text{Vo} + 20 - 2\text{Vo} = 2\text{Vo}$$
$$\therefore \text{Vo} = \frac{\text{Vi} + 20}{5}$$

- 12. In the diode circuit, the diode has the reverse characteristics as shown. The diode equation is $I = Io \exp [(V/25mV) 1]$.
- (a) Sketch the circuit model of the diode at breakdown.
- (b) Find I1 if Vi = -1V.
- (c) Find I1 if Vi = 2V.
- (d) Find I2 if Vi = 16V. (35)



a

b

Vi = -1V, : Vo = -0.5V
:
$$I_1 = -I_0 (e^{\frac{0.5V}{25mV}} - 1)$$

= -0.01x10⁻¹² $A(e^{\frac{500m}{25m}} - 1) = -4.85x10^{-6} A$

c

$$I_1 = I_0 = 0.01 \times 10^{-12} \text{ A}$$

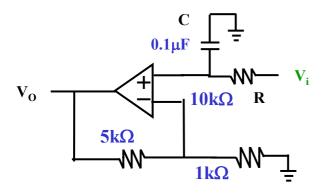
d Vi = 16V, : Vo = 8V, D breakdown

$$\frac{16 - \mathbf{Vo}}{1\mathbf{k}} = \frac{\mathbf{Vo} - 7}{5} + \frac{\mathbf{Vo}}{1\mathbf{k}}$$

$$16 - \mathbf{Vo} = 200(\mathbf{Vo} - 7) + \mathbf{Vo}$$

$$\mathbf{Vo} = \frac{1400 + 16}{202} \cong 7.01\mathbf{V}$$

$$\therefore \mathbf{I2} = \frac{\mathbf{Vo}}{\mathbf{R_L}} \cong \frac{7.01}{1\mathbf{k}} = 7.01\mathbf{mA}$$



$$\mathbf{V}_{2} = \mathbf{V}\mathbf{i} \frac{\frac{1}{\mathbf{j}\omega\mathbf{C}}}{\mathbf{R} + \frac{1}{\mathbf{j}\omega\mathbf{C}}} = \frac{\mathbf{V}\mathbf{i}}{1 + \mathbf{j}\omega\mathbf{C}\mathbf{R}}$$

$$\therefore \mathbf{V}_{0} = \mathbf{V}_{2}(1 + \frac{5\mathbf{k}}{1\mathbf{k}}) = 6\mathbf{V}_{2} = 6\frac{\mathbf{V}\mathbf{i}}{1 + \mathbf{j}\omega\mathbf{C}\mathbf{R}}$$

$$\therefore \mathbf{G} = \frac{\mathbf{V}_{0}}{\mathbf{V}_{i}} = \frac{6}{1 + \mathbf{j}\omega\mathbf{C}\mathbf{R}}$$

- 13. Given the filter circuit. The op amp is ideal.
- (a) Obtain the complex transfer function G (=Vo/Vi) in terms of j ω , C and R.
- (b) Find the cut-off frequency (in rad/s) and the DC gain (value of G when Vi is a DC voltage) of the filter.
- (c) Sketch |Vo/Vi| in dB versus angular frequency ω. Label clearly all intercepts. Given |G| in $dB = 20\log_{10} |G|$.
- (d) Is it a low pass filter? Find also the pole and zero of the filter. (38)

At cut off frequency $\therefore G = \frac{V_o}{V_c} = \frac{6}{1+i}$

$$\omega_{o}$$
CR = 1
 $\therefore \omega_{o} = \frac{1}{CR} = \frac{1}{0.1\mu(10k)} = 1 \text{krad/s}$

DC gain
$$G = 6$$

At low frequency, $\omega \sim 0$

|G| in dB =
$$20 \log_{10} 6 \cong 15.6$$
 dB

At cut-off frequency,

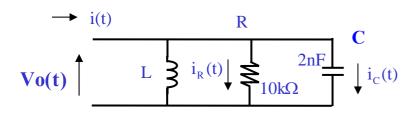
|G| in dB = $20 \log_{10} \frac{6}{\sqrt{2}} \cong 12.6$ dB

low pass filter

- 15. In the following LCR circuit,
- (a) find the resonant frequency (in rad/s and in Hz), Q-factor, bandwidth, upper and lower cut-off frequencies (all in rad/s) of the LCR circuit.
- (b) If $i(t) = \sqrt{8\cos\omega t}$ mA find Vo(t) and iC(t) at resonance. (36)

Lower f :
$$\omega_1 = \omega_0 - \frac{BW}{2} = 4950k \text{ rad/s}$$

Upperf
$$\therefore \omega_2 = \omega_0 + \frac{BW}{2} = 5050k \text{ rad/s}$$



$$\therefore \omega_{O} = \frac{1}{\sqrt{LC}} = \frac{1}{\sqrt{L*2n}} = 5M \text{ rad/s and } 795.78\text{kHz}$$

Hence L =
$$\frac{1}{(5M)^2 * 2n}$$
 = 0.02mH

:. Q factor =
$$\frac{Q}{P} = \frac{R}{\omega_0 L} = \frac{10k}{5M(0.02m)} = 100$$

$$\therefore BW = \frac{\omega_0}{Q \, factor} = \frac{5M}{100} = 50k \, rad/s \, or \, 7.96kHz$$

If i is 2mA rms

$$\therefore i_R = 2m \text{ Arms}$$

∴
$$i_R = 2m \text{ Arms}$$

∴ Vo = 2mA * 10kΩ = 20 Vrms

$$\therefore i_C = Q factor * i_R = 200 \text{ mArms}$$

$$\therefore Vo(t) = 20\sqrt{2}\cos 5Mt V$$

$$\therefore i_{C}(t) = 200\sqrt{2}\cos(5Mt + 90^{\circ}) \,\mathrm{mA}$$

